Scopus

Author details

About Scopus Author Identific

Keturn to search results	s 1 of 1			🖨 Print	⊠ Em
Chowdhury,	Srabanti		Follow this Author	h-index: ⊕ View h	-graph
UC Davis, Department Engineering, Davis, Un Author ID: 366097749		View poten	tial author matches		
Other name formats:	Chowdury, S. Chowdhury, S.			Documents by author	
Subject area:	Materials Science Engineering Physic Biochemistry, Genetics and Molecular Biole	, .	thematics Energy	42 Analyze author	output
Document and	Brochemistry, Genetics and morecalar Brok	751		Total citations	
citation trends:				404 by 297 documents	
∴ Get citation alerts	+ Add to ORCID Request authorized Add to ORCID	or detail corrections		View citation o	verview
42 Documents	Cited by 297 documents 94 of	co-authors Author history			
View in search results	format >		Sort on:	Date (newest)	~
Export all Add all	to list Set document alert Set docu	iment feed			
Document title		Authors	Year Source	C	Cited by
Stability of alloyed and GaN at high temperate	nonalloyed ohmic contacts to n-type ure in air	Zhao, S., Gao, J., Wang, S., (), Goodnick, S., Chowdhury, S.	2017 Japanese Journal 56(12),126502	of Applied Physics	0
View abstract ✓ View	at Publisher Find it 6 NTU Related	documents			
	gineering of GaN HETs for RF Full-Band Monte Carlo Simulations	Soligo, R., Sabatti, F., Chowdhury, S., Saraniti, M.	2017 IEEE Transaction 64(11),8061004,		0
View abstract ✓ View	at Publisher Find it 6 NTU Related	documents			
Demonstration of GaN Self-Aligned Process	Static Induction Transistor (SIT) Using	Li, W., Ji, D., Tanaka, R., (), Laurent, M., Chowdhury, S.	2017 IEEE Journal of t 5(6),8031374, pp Open Access		1
View abstract ✓ View	at Publisher Find it 6 NTU Related	documents			
Impact of Trench Dime GaN Vertical Trench M	ensions on the Device Performance of MOSFETs	Gupta, C., Ji, D., Chan, S.H., (), Chowdhury, S., Mishra, U.K.	2017 IEEE Electron De 38(11),8026114,		0
View abstract ✓ View	at Publisher Find it 6 NTU Related	documents			
Al2O3dielectric layers of surface conductivity	on H-terminated diamond: Controlling	Yang, Y., Koeck, F.A., Dutta, M., (), Chowdhury, S., Nemanich, R.J.	2017 Journal of Applie 122(15),155304	ed Physics	0
View abstract ✓ View	rat Publisher Find it 6 NTU Related	documents			
	Ga2O3 interface and conduction band a Sol-gel process of deposition	Gao, J., Kaya, A., Chopdekar, R.V., (), Islam, M.S., Chowdhury, S.	2017 Device Research Digest, DRC 7999447	Conference - Conference	0
View abstract ✓ View	at Publisher Find it S NTU Related	documents			
	a normally-off in-situ oxide, GaN al trench MOSFET (OG-FET)	Ji, D., Gupta, C., Agarwal, A., (), Mishra, U.K., Chowdhury, S.	2017 Device Research Digest, DRC 7999442	Conference - Conference	1
View abstract ✓ View	at Publisher Find it 6 NTU Related	documents			

Document title	Authors	Year	Source	Cited by
Nitride Semiconductors	Doolittle, A., Palacios, T., Keller, S., (), Chowdhury, S., Shen, SC.	2017	Physica Status Solidi (B) Basic Research 254(8),1770245	(
View at Publisher Find it 6 NTU				
Analysis of the reverse I-V characteristics of diamond-based PIN diodes	Saremi, M., Hathwar, R., Dutta, M., (), Chowdhury, S., Goodnick, S.M.	2017	Applied Physics Letters 111(4),043507	C
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
Dispersion free 450-V p GaN-gated CAVETs with mg-ion implanted blocking layer	Mandal, S., Agarwal, A., Ahmadi, E., (), Keller, S., Chowdhury, S.	2017	IEEE Electron Device Letters 38(7),7935531, pp. 933-936	3
View abstract ✓ View at Publisher Find it 6 NTU Related	documents			
High Voltage Diodes in Diamond Using (100)-A nd (111) -Substrates	Dutta, M., Koeck, F.A.M., Li, W., Nemanich, R.J., Chowdhury, S.	2017	IEEE Electron Device Letters 38(5),7875438, pp. 600-603	2
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
An Investigation of Electrical and Dielectric Parameters of Sol-Gel Process Enabled β -Ga2O3as a Gate Dielectric Material	Kaya, A., Mao, H., Gao, J., (), Chowdhury, S., Islam, M.S.	2017	IEEE Transactions on Electron Devices 64(5),7883897, pp. 2047-2053	2
View abstract ✓ View at Publisher Find it 6 NTU Related	documents			
Normally off Trench CAVET with Active Mg-Doped GaN as Current Blocking Layer	Ji, D., Laurent, M.A., Agarwal, A., (), Keller, S., Chowdhury, S.	2017	IEEE Transactions on Electron Devices 64(3),7786867, pp. 805-808	8
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
A study of the effect of surface pretreatment on atomic layer deposited Al ² O ³ interface with GaN	Gao, J., Li, W., Mandal, S., Chowdhury, S.	2017	Proceedings of SPIE - The International Society for Optical Engineering 10381,1038103	0
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
Comparative study of CAVET with dielectric and p-GaN gate and Mg ion-implanted current blocking layer	Mandal, S., Agarwal, A., Ahmadi, E., (), Keller, S., Chowdhury, S.	2017	Proceedings of SPIE - The International Society for Optical Engineering 10381,1038108	0
View abstract ✓ View at Publisher Find it 6 NTU Related	documents			
Ultrawide-Bandgap Semiconductors: Research Opportunities and Challenges	Tsao, J.Y., Chowdhury, S., Hollis, M.A., (), Wraback, M., Simmons, J.A.	2017	Advanced Electronic Materials Article in Press	0
View abstract ✓ View at Publisher Find it ⊘ NTU			Article in Press	
Potential of GaN vertical JFETs presented through a comprehensive discussion of dynamic performance compared to SiC JFETs	Ji, D., Li, W., Chowdhury, S.	2016	WiPDA 2016 - 4th IEEE Workshop on Wic Bandgap Power Devices and Applications 7799920, pp. 114-117	de 0
View abstract ✓ View at Publisher Find it 5 NTU Related	documents			
Design and fabrication of a 1.2 kV GaN-based MOS vertical transistor for single chip normally off operation	Li, W., Chowdhury, S.	2016	Physica Status Solidi (A) Applications and Materials Science 213(10), pp. 2714-2720	5
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
Dynamic Modeling and Power Loss Analysis of High- Frequency Power Switches Based on GaN CAVET	Ji, D., Yue, Y., Gao, J., Chowdhury, S.	2016	IEEE Transactions on Electron Devices 63(10),7558241, pp. 4011-4017	5
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
Demonstration of Diamond-Based Schottky p-i-n Diode with Blocking Voltage > 500 v	Dutta, M., Koeck, F.A.M., Hathwar, R., (), Nemanich, R.J., Chowdhury, S.	2016	IEEE Electron Device Letters 37(9),7515223, pp. 1170-1173	5
View abstract ✓ View at Publisher Find it ⑤ NTU Related	documents			
Display: 20 results per page	<u>1</u> 2 3		^	Top of page

The data displayed above is compiled exclusively from documents indexed in the Scopus database. To request corrections to any inaccuracies or provide any further feedback, please use the Author Feedback Wizard.

About Scopus Language Customer Service

What is Scopus日本語に切り替えるHelpContent coverage切換到简体中文Contact us

Scopus blog切換到繁體中文Scopus APIРусский язык

ELSEVIER

Privacy matters

Terms and conditions Privacy policy

Copyright \circledcirc 2018 Elsevier B.V. All rights reserved. Scopus \circledcirc is a registered trademark of Elsevier

B.V.

Cookies are set by this site. To decline them or learn more, visit our Cookies page.

≪ RELX Grou